FINAL

Am29F200T/Am29F200B

2 Megabit (262,144 x 8-Bit/131,072 x 16-Bit) CMOS 5.0 Volt-only, Sector Erase Flash Memory

Advanced Micro Devices

DISTINCTIVE CHARACTERISTICS

- **5.0 V ± 10% for read and write operations**
  - — Minimizes system level power requirements
- **Compatible with JEDEC-standards**
  - — Pinout and software compatible with single-power-supply flash
  - — Superior inadvertent write protection
- **Package options**
  - — 44-pin SO
  - — 48-pin TSOP
- **Minimum 100,000 write/erase cycles guaranteed**
- **High performance**
  - — 70 ns maximum access time
- **Sector erase architecture**
  - — One 16 Kbyte, two 8 Kbytes, one 32 Kbyte, and three 64 Kbytes
  - — Any combination of sectors can be erased. Also supports full chip erase.
- **Sector protection**
  - — Hardware method that disables any combination of sectors from write or erase operations. Implemented using standard PROM programming equipment.
- **Embedded Erase Algorithms**
  - — Automatically pre-programs and erases the chip or any sector
- **Embedded Program Algorithms**
  - — Automatically programs and verifies data at specified address
- **$\overline{\text{Data}}$ Polling and Toggle Bit feature for detection of program or erase cycle completion**
- **Ready/$\overline{\text{Busy}}$ output (RY/$\overline{\text{BY}}$)**
  - — Hardware method for detection of program or erase cycle completion
- **Erase Suspend/Resume**
  - — Supports reading data from a sector not being erased
- **Low power consumption**
  - — 20 mA typical active read current for Byte Mode
  - — 28 mA typical active read current for Word Mode
  - — 30 mA typical program/erase current
- **Enhanced power management for standby mode**
  - — 25 µA typical standby current
- **Boot Code Sector Architecture**
  - — T = Top sector
  - — B = Bottom sector
- **Hardware $\overline{\text{RESET}}$ pin**
  - — Resets internal state machine to the read mode

GENERAL DESCRIPTION

The Am29F200 is a 2 Mbit, 5.0 Volt-only Flash memory organized as 256 Kbytes of 8 bits each or 128 words of 16 bits each. The 2 Mbits of data is divided into 7 sectors of one 16 Kbyte, two 8 Kbyte, one 32 Kbyte, and three 64 Kbytes, for flexible erase capability. The 8 bits of data will appear on DQ0–DQ7 or 16 bits on DQ0–DQ15. The Am29F200 is offered in 44-pin SO and 48-pin TSOP packages. This device is designed to be programmed in-system with the standard system 5.0 Volt V_{CC} supply. 12.0 Volt V_{PP} is not required for program or erase operations. The device can also be reprogrammed in standard EPROM programmers.

The standard Am29F200 offers access times of 70 ns, 90 ns, 120 ns, and 150 ns, allowing operation of high-speed microprocessors without wait states. To eliminate bus contention the device has separate chip enable ($\overline{\text{CE}}$), write enable ($\overline{\text{WE}}$) and output enable ($\overline{\text{OE}}$) controls.

The Am29F200 is entirely command set compatible with the JEDEC single-power-supply Flash standard. Commands are written to the command register using standard microprocessor write timings. Register contents serve as input to an internal state-machine which controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations. Reading data out of the device is similar to reading from 12.0 Volt Flash or EPROM devices.

The Am29F200 is programmed by executing the program command sequence. This will invoke the Embedded Program Algorithm which is an internal algorithm that automatically times the program pulse widths and verifies proper cell margin. Erase is accomplished by executing the erase command sequence. This will invoke the Embedded Erase Algorithm which is an internal algorithm that automatically preprograms the array if

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it is not already programmed before executing the erase operation. During erase, the device automatically times the erase pulse widths and verifies proper cell margin.

This device also features a sector erase architecture. This allows for sectors of memory to be erased and reprogrammed without affecting the data contents of other sectors. A sector is typically erased and verified within 1.5 seconds. The Am29F200 is erased when shipped from the factory.

The Am29F200 device also features hardware sector protection. This feature will disable both program and erase operations in any combination of eleven sectors of memory.

AMD has implemented an Erase Suspend feature that enables the user to put erase on hold for any period of time to read data from a sector that was not being erased. Thus, true background erase can be achieved.

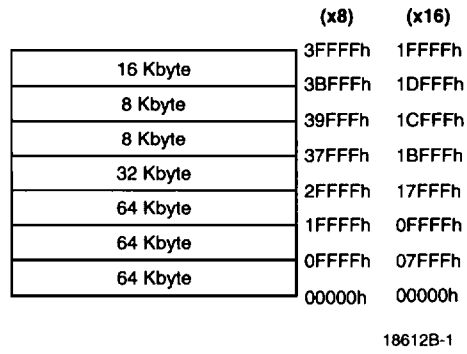
The device features single 5.0 Volt power supply operation for both read and write functions. Internally generated and regulated voltages are provided for the program and erase operations. A low V_{CC} detector automatically inhibits write operations during power transitions. The end of program or erase is detected by the RY/$\overline{BY}$ pin. $\overline{Data}$ Polling of DQ7, or by the Toggle Bit (DQ6). Once the end of a program or erase cycle has been completed, the device automatically resets to the read mode.

The Am29F200 also has a hardware $\overline{RESET}$ pin. When this pin is driven low, execution of any Embedded Program Algorithm or Embedded Erase Algorithm will be terminated. The internal state machine will then be reset into the read mode. The $\overline{RESET}$ pin may be tied to the system reset circuitry. Therefore, if a system reset occurs during the Embedded Program Algorithm or Embedded Erase Algorithm, the device will be automatically reset to the read mode and will have erroneous data stored in the address locations being operated on. These locations will need re-writing after the Reset. Resetting the device will enable the system's microprocessor to read the boot-up firmware from the Flash memory.

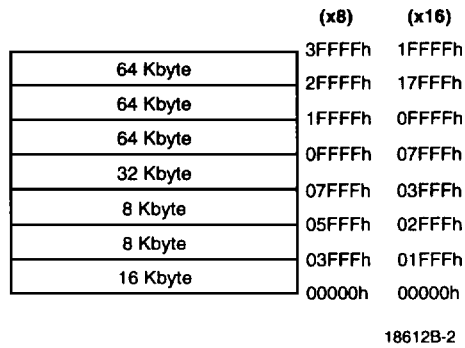
AMD's Flash technology combines years of Flash memory manufacturing experience to produce the highest levels of quality, reliability and cost effectiveness. The Am29F200 memory electrically erases all bits within a sector simultaneously via Fowler-Nordhiem tunneling. The bytes/words are programmed one byte/word at a time using the EPROM programming mechanism of hot electron injection.

Flexible Sector-Erase Architecture

- One 16 Kbyte, two 8 Kbytes, one 32 Kbyte, and three 64 Kbyte sectors
- Individual-sector or multiple-sector erase capability
- Sector protection is user definable



Am29F200T Sector Architecture

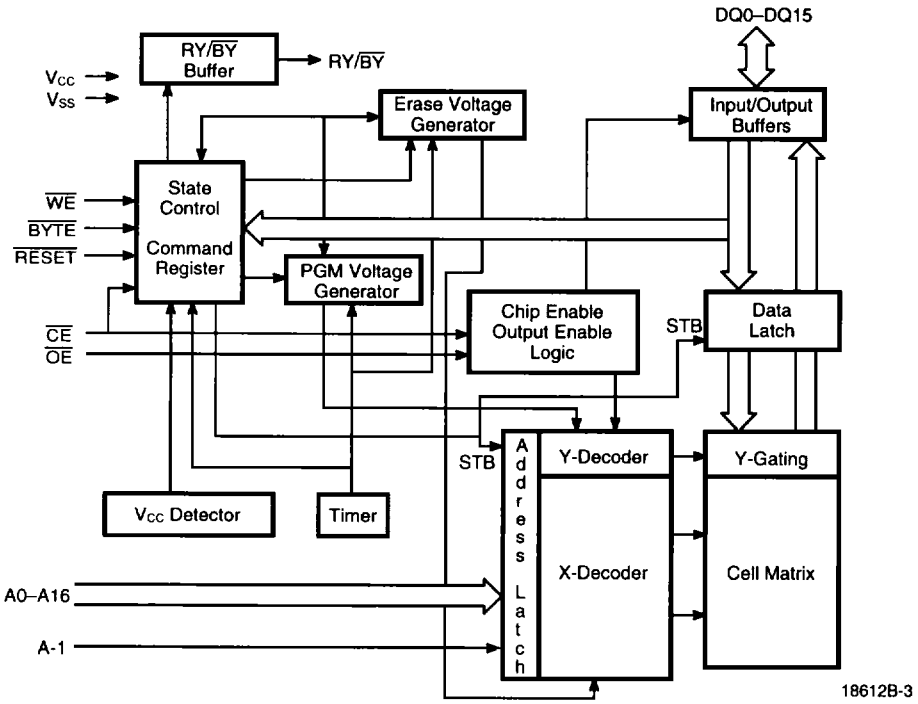


Am29F200B Sector Architecture

PRODUCT SELECTOR GUIDE

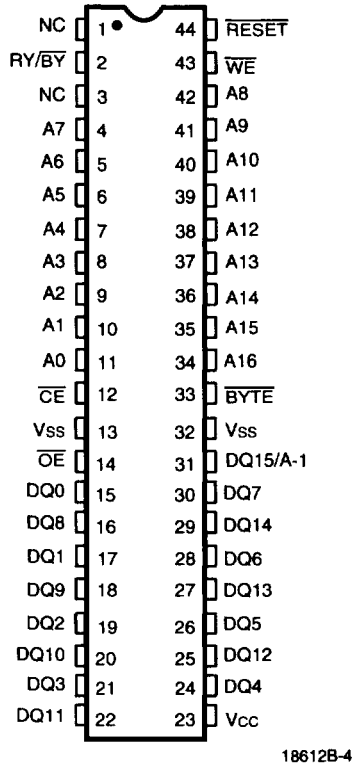
Family Part No:	Am29F200			
Ordering Part No: V_{CC} = 5.0 V ± 5%	-75			
V_{CC} = 5.0 V ± 10%		-90	-120	-150
Max Access Time (ns)	70	90	120	150
$\overline{CE}$ ($\overline{E}$) Access (ns)	70	90	120	150
$\overline{OE}$ ($\overline{G}$) Access (ns)	30	35	50	55

BLOCK DIAGRAM



CONNECTION DIAGRAMS

SO



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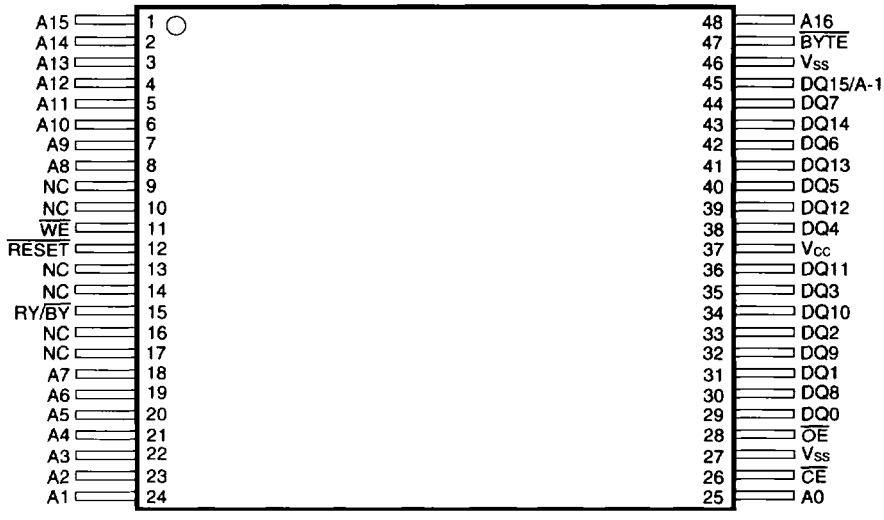
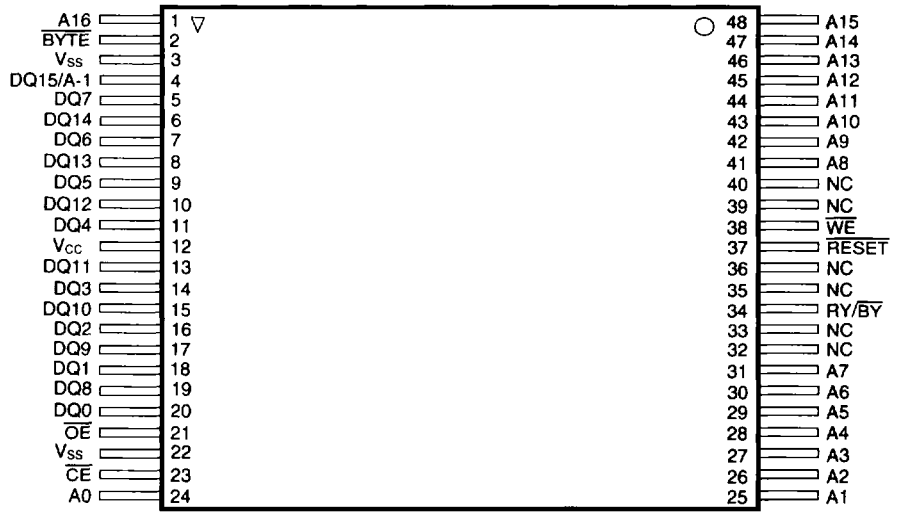
CONNECTION DIAGRAMS



Standard TSOP 18612B-5

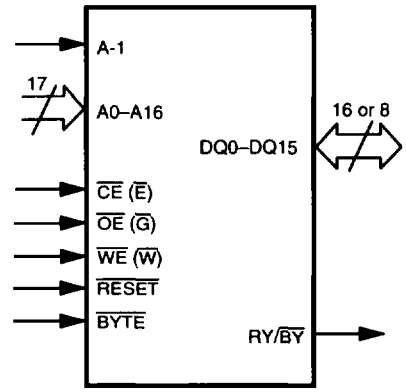


Reverse TSOP 18612B-6

PIN CONFIGURATION

A-1, A0–A16	=	17 Addresses
$\overline{BYTE}$	=	Selects 8-bit or 16-bit mode
$\overline{CE}$	=	Chip Enable
DQ0–DQ15	=	16 Data Inputs/Outputs
NC	=	Pin Not Connected Internally
$\overline{OE}$	=	Output Enable
$\overline{RESET}$	=	Hardware Reset Pin, Active Low
RY/$\overline{BY}$	=	Ready/$\overline{Busy}$ Output
V_{CC}	=	+5.0 Volt Single-Power Supply (±10% for -90, -120, -150) or (±5% for -75)
V_{SS}	=	Device Ground
$\overline{WE}$	=	Write Enable

LOGIC SYMBOL



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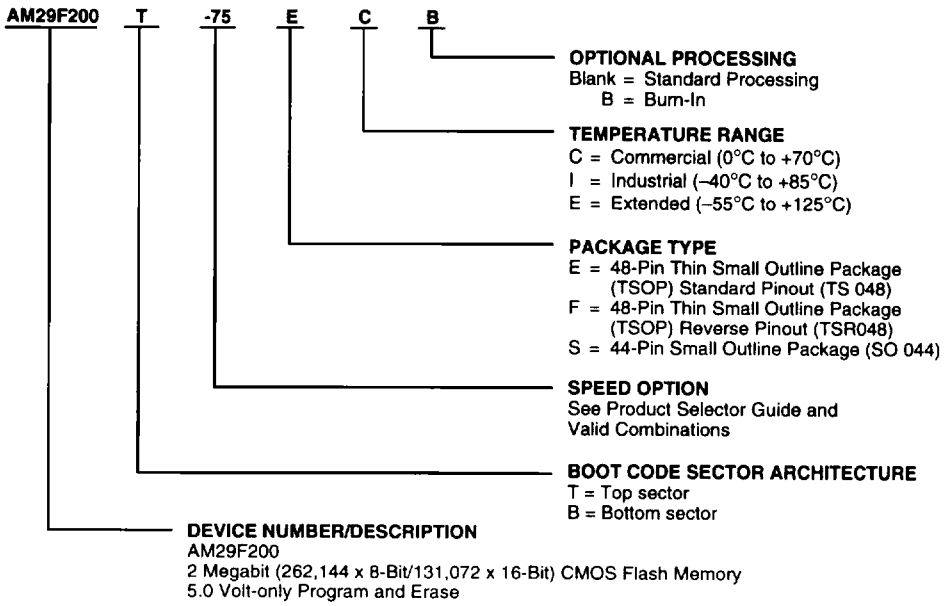
ORDERING INFORMATION

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:



Valid Combinations	
AM29F200T/B-75	EC, FC, SC
AM29F200T/B-90	EC, EI, FC, FI, EE, EEB, FE, FEB, SC, SI, SE, SEB
AM29F200T/B-120	
AM29F200T/B-150	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Table 1.1 Am29F200 User Bus Operations ($\overline{BYTE}$ = V_{IH})

Operation	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	A0	A1	A6	A9	DQ0–DQ15	$\overline{RESET}$
Autoselect, AMD Manuf. Code (1)	L	L	H	L	L	L	V_{ID}	Code	H
Autoselect Device Code (1)	L	L	H	H	L	L	V_{ID}	Code	H
Read (3)	L	L	H	A0	A1	A6	A9	D_{OUT}	H
Standby	H	X	X	X	X	X	X	HIGH Z	H
Output Disable	L	H	H	X	X	X	X	HIGH Z	X
Write	L	H	L	A0	A1	A6	A9	D_{IN}	H
Unable Sector Protect	L	V_{ID}	L	X	X	X	V_{ID}	X	H
Verify Sector Protect (2)	L	L	H	L	H	L	V_{ID}	Code	H
Temporary Sector Unprotect	X	X	X	X	X	X	X	X	V_{ID}
Hardware Reset	X	X	X	X	X	X	X	HIGH Z	L

Table 1.2 Am29F200 User Bus Operations ($\overline{BYTE}$ = V_{IL})

Operation	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	A0	A1	A6	A9	DQ0–DQ7	DQ8–DQ15	$\overline{RESET}$
Autoselect, AMD Manuf. Code (1)	L	L	H	L	L	L	V_{ID}	Code	HIGH Z	H
Autoselect Device Code (1)	L	L	H	H	L	L	V_{ID}	Code	HIGH Z	H
Read (3)	L	L	H	A0	A1	A6	A9	D_{OUT}	HIGH Z	H
Standby	H	X	X	X	X	X	X	HIGH Z	HIGH Z	H
Output Disable	L	H	H	X	X	X	X	HIGH Z	HIGH Z	H
Write	L	H	L	A0	A1	A6	A9	D_{IN}	HIGH Z	H
Enable Sector Protect	L	V_{ID}	L	X	X	X	V_{ID}	X	HIGH Z	H
Verify Sector Protect (2)	L	L	H	L	H	L	V_{ID}	Code	HIGH Z	H
Temporary Sector Unprotect	X	X	X	X	X	X	X	X	HIGH Z	V_{ID}
Hardware Reset	X	X	X	X	X	X	X	HIGH Z	HIGH Z	L

Legend:

L = logic 0, H = logic 1, X = Don't Care. See Characteristics for voltage levels.

Notes:

1. *Manufacturer and device codes may also be accessed via a command register write sequence. Refer to Table 4.*
2. *Refer to the section on Sector Protection.*
3. *$\overline{WE}$ can be V_{IL} if $\overline{OE}$ is V_{IL}. $\overline{OE}$ at V_{IL} initiates the write operations.*

Read Mode

The Am29F200 has two control functions which must be satisfied in order to obtain data at the outputs. $\overline{CE}$ is the power control and should be used for device selection. $\overline{OE}$ is the output control and should be used to gate data to the output pins if a device is selected.

Address access time (t_{ACC}) is equal to the delay from stable addresses to valid output data. The chip enable access time (t_{CE}) is the delay from stable addresses and stable $\overline{CE}$ to valid data at the output pins. The output enable access time is the delay from the falling edge of $\overline{OE}$ to valid data at the output pins (assuming the addresses have been stable for at least t_{ACC}–t_{OE} time).

Standby Mode

There are two ways to implement the standby mode on the Am29F200 device, both using the $\overline{CE}$ pin.

A CMOS standby mode is achieved with the $\overline{CE}$ input held at $V_{CC} \pm 0.5$ V. Under this condition the current is typically reduced to less than 100 µA. A TTL standby mode is achieved with the $\overline{CE}$ pin held at V_{IH}. Under this condition the current is typically reduced to 1 mA.

In the standby mode the outputs are in the high impedance state, independent of the $\overline{OE}$ input.

Output Disable

With the $\overline{OE}$ input at a logic high level (V_{IH}), output from the device is disabled. This will cause the output pins to be in a high impedance state.

Autoselect

The autoselect mode allows the reading of a binary code from the device and will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional over the entire temperature range of the device.

To activate this mode, the programming equipment must force V_{ID} (11.5 V to 12.5 V) on address pin A9. Two identifier bytes may then be sequenced from the device outputs by toggling address A0 from V_{IL} to V_{IH}. All addresses are don't cares except A0, A1, and A6 (see Table 2.1).

The manufacturer and device codes may also be read via the command register, for instances when the Am29F200 is erased or programmed in a system without access to high voltage on the A9 pin. The command sequence is illustrated in Table 4 (see Autoselect Command Sequence).

Byte 0 (A0 = V_{IL}) represents the manufacturer's code (AMD=01H) and byte 1 (A0 = V_{IH}) the device identifier code (Am29F200T = 51H and Am29F200B = 57H for x8 mode; Am29F200T = 2251H and Am29F200B = 2257H for x16 mode). These two bytes/words are given in the table below. All identifiers for manufacturer and device will exhibit odd parity with DQ7 defined as the parity bit. In order to read the proper device codes when executing the Autoselect, A1 must be V_{IL} (see Tables 2.1 and 2.2).

The autoselect mode also facilitates the determination of sector protection in the system. By performing a read operation at the address location XX02H with the higher order address bits A12 – A17 set to the desired sector address, the device will return 01H for a protected sector and 00H for a non-protected sector.

Table 2.1 Am29F200 Sector Protection Verify Autoselect Codes

Type			A12–A16	A6	A1	A0	Code (HEX)
Manufacturer Code–AMD			X	V_{IL}	V_{IL}	V_{IL}	01H
Am29F200 Device Code	Am29F200T	Byte	X	V_{IL}	V_{IL}	V_{IH}	51H
		Word					2251H
	Am29F200B	Byte	X	V_{IL}	V_{IL}	V_{IH}	57H
		Word					2257H
Sector Protection			Sector Address	V_{IL}	V_{IH}	V_{IL}	01H*

**Outputs 01H at protected sector addresses*

Table 2.2 Expanded Autoselect Code Table

Type		Code	DQ 15	DQ 14	DQ 13	DQ 12	DQ 11	DQ 10	DQ 9	DQ 8	DQ 7	DQ 6	DQ 5	DQ 4	DQ 3	DQ 2	DQ 1	DQ 0
Manufacturer Code–AMD		01H	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1
Am29F200 Device Code	Am29F200T(B)	51H	A–1	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	0	1	0	1	0	0	0	1
	(W)	2251H	0	0	1	0	0	0	1	0	0	1	0	1	0	0	0	1
	Am29F200B(B)	57H	A–1	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	HI–Z	1	0	1	0	0	0	1	0
	(W)	2257H	0	0	1	0	0	0	1	0	1	0	1	0	0	0	1	0
Sector Protection		01H	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

(B) – Byte mode

(W) – Word mode

Table 3.1 Sector Address Tables (Am29F200T)

	A16	A15	A14	A13	A12	(x8) Address Range	(x16) Address Range
SA0	0	0	X	X	X	00000h–0FFFFh	00000h–07FFFh
SA1	0	1	X	X	X	10000h–1FFFFh	08000h–0FFFFh
SA2	1	0	X	X	X	20000h–2FFFFh	10000h–17FFFh
SA3	1	1	0	X	X	30000h–37FFFh	18000h–1BFFFh
SA4	1	1	1	0	0	38000h–39FFFh	1C000h–1CFFFh
SA5	1	1	1	0	1	3A000h–3BFFFh	1D000h–1DFFFh
SA6	1	1	1	1	X	3C000h–3FFFFh	1E000h–1FFFFh

Table 3.2 Sector Address Tables (Am29F200B)

	A16	A15	A14	A13	A12	(x8) Address Range	(x16) Address Range
SA0	0	0	0	0	X	00000h–03FFFh	00000h–01FFFh
SA1	0	0	0	1	0	04000h–05FFFh	02000h–02FFFh
SA2	0	0	0	1	1	06000h–07FFFh	03000h–03FFFh
SA3	0	0	1	X	X	08000h–0FFFFh	04000h–07FFFh
SA4	0	1	X	X	X	10000h–1FFFFh	08000h–0FFFFh
SA5	1	0	X	X	X	20000h–2FFFFh	10000h–17FFFh
SA6	1	1	X	X	X	30000h–3FFFFh	18000h–1FFFFh

Write

Device erasure and programming are accomplished via the command register. The contents of the register serve as inputs to the internal state machine. The state machine outputs dictate the function of the device.

The command register itself does not occupy any addressable memory location. The register is a latch used to store the commands, along with the address and data information needed to execute the command. The command register is written to by bringing $\overline{WE}$ to V_{IL}, while $\overline{CE}$ is at V_{IL} and $\overline{OE}$ is at V_{IH}. Addresses are latched on the falling edge of $\overline{WE}$ or $\overline{CE}$, whichever happens later; while data is latched on the rising edge of $\overline{WE}$ or $\overline{CE}$, whichever happens first. Standard microprocessor write timings are used.

Refer to AC Write Characteristics and the Erase/Programming Waveforms for specific timing parameters.

Sector Protection

The Am29F200 features hardware sector protection. This feature will disable both program and erase operations in any combination of ten sectors of memory. The sector protect feature is enabled using *programming equipment at the user's site.* The device is shipped with all sectors unprotected. Alternatively, AMD may program and protect sectors in the factory prior to shipping the device (AMD's ExpressFlash Service).

It is possible to determine if a sector is protected in the system by writing an Autoselect command. Performing a read operation at the address location XX02H, where the higher order address bits (A16, A15, A14, A13, and A12) is the desired sector address, will produce a logical "1" at DQ0 for a protected sector. See Table 2.1 for Autoselect codes.

Temporary Sector Unprotect

This feature allows temporary unprotection of previously protected sectors of the Am29F200 device in order to change data in-system. The Sector Unprotect mode is activated by setting the $\overline{RESET}$ pin to high voltage (12 V). During this mode, formerly protected sectors can be programmed or erased by selecting the sector addresses. Once the 12 V is taken away from the $\overline{RESET}$ pin, all the previously protected sectors will be protected again. Refer to Figures 17 and 18.

Command Definitions

Device operations are selected by writing specific address and data sequences into the command register. **Writing incorrect address and data values or writing them in the improper sequence will reset the device to the read mode.** Table 4 defines the valid register command sequences. Note that the Erase Suspend (B0H) and Erase Resume (30H) commands are valid only while the Sector Erase operation is in progress. Moreover, both Reset/Read commands are functionally equivalent, resetting the device to the read mode.

Table 4. Am29F200 Command Definitions (Notes 1–7)

Command Sequence Read/Reset		Bus Write Cycles Req'd	First Bus Write Cycle		Second Bus Write Cycle		Third Bus Write Cycle		Fourth Bus Read/Write Cycle		Fifth Bus Write Cycle		Sixth Bus Write Cycle	
			Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
Reset/Read		1	XXXXH	F0H										
Reset/Read	Word	4	5555H	AAH	2AAAH	55H	5555H	F0H	RA	RD				
	Byte		AAAAH		5555H		AAAAH							
Autoselect	Word	4	5555H	AAH	2AAAH	55H	5555H	90H	01H	2251H (T Device ID) 2257H (B Device ID)				
	Byte		AAAAH		5555H		AAAAH			51H (T Device ID) 57H (B Device ID)				
	Word/Byte								00H	01H (T/B Manuf. ID)				
Program	Word	4	5555H	AAH	2AAAH	55H	5555H	A0H	PA	Data				
	Byte		AAAAH		5555H		AAAAH							
Chip Erase	Word	6	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	5555H	10H
	Byte		AAAAH		5555H		AAAAH		AAAAH		5555H		AAAAH	
Sector Erase	Word	6	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	SA	30H
	Byte		AAAAH		5555H		AAAAH		AAAAH		5555H			
Sector Erase Suspend			Erase can be suspended during sector erase with Addr (don't care), Data (B0H)											
Sector Erase Resume			Erase can be resumed after suspend with Addr (don't care), Data (30H)											

Notes:

1. *Bus operations are defined in Table 1.1.*
2. *RA = Address of the memory location to be read.*
   PA = Address of the memory location to be programmed. Addresses are latched on the falling edge of the $\overline{WE}$ pulse.
   SA = Address of the sector to be erased. The combination of A16, A15, A14, A13, and A12 will uniquely select any sector.
3. *RD = Data read from location RA during read operation.*
   PD = Data to be programmed at location PA. Data is latched on the rising edge of $\overline{WE}$.
4. *Reading from non-erasing sectors is allowed in the Erase Suspend mode.*
5. *Address bit A15 = X = Don't Care for all address commands except for Program Address (PA) and Sector Address (SA). Write Sequences may be initiated with A15 in either state.*
6. *Address bits A16 = X = Don't Care for all address commands except for Program Address (PA) and Sector Address (SA).*
7. *The system should generate the following address patterns:*
   Word Mode: 5555H or 2AAAH to addresses A0 – A14
   Byte Mode: AAAAH or 5555H to addresses A-1 – A14.

Read/Reset Command

The read or reset operation is initiated by writing the read/reset command sequence into the command register. Microprocessor read cycles retrieve array data from the memory. The device remains enabled for reads until the command register contents are altered.

The device will automatically power-up in the read/reset state. In this case, a command sequence is not required to read data. Standard microprocessor read cycles will retrieve array data. This default value ensures that no spurious alteration of the memory content occurs during the power transition. Refer to the AC Read Characteristics and Waveforms for the specific timing parameters.

Autoselect Command

Flash memories are intended for use in applications where the local CPU can alter memory contents. As such, manufacture and device codes must be accessible while the device resides in the target system. PROM programmers typically access the signature codes by raising A9 to a high voltage. However, multiplexing high voltage onto the address lines is not generally a desirable system design practice.

The device contains an autoselect command operation to supplement traditional PROM programming methodology. The operation is initiated by writing the autoselect command sequence into the command register. Follow-

ing the command write, a read cycle from address XX00H retrieves the manufacture code of 01H. A read cycle from address XX01H returns the device code (Am29F200T = 51H and Am29F200B = 57H for x8 mode; Am29F200T = 2251H and Am29F200B = 2257H for x16 mode) (see Tables 2.1 and 2.2).

All manufacturer and device codes will exhibit odd parity with DQ7 defined as the parity bit.

Furthermore, the write protect status of sectors can be read in this mode. Scanning the sector addresses (A16, A15, A14, A13, and A12) while (A6, A1, A0) = (0, 1, 0) will produce a logical "1" at device output DQ0 for a protected sector.

To terminate the operation, it is necessary to write the read/reset command sequence into the register.

Byte/Word Programming

The device is programmed on a byte-by-byte (or word-by-word) basis. Programming is a four bus cycle operation. There are two "unlock" write cycles. These are followed by the program set-up command and data write cycles. Addresses are latched on the falling edge of $\overline{CE}$ or $\overline{WE}$, whichever happens later and the data is latched on the rising edge of $\overline{CE}$ or $\overline{WE}$, whichever happens first. The rising edge of $\overline{CE}$ or $\overline{WE}$ (whichever happens first) begins programming using the Embedded Program Algorithm. Upon executing the algorithm, the system is *not* required to provide further controls or timings. The device will automatically provide adequate internally generated program pulses and verify the programmed cell margin.

The automatic programming operation is completed when the data on DQ7 (also used as $\overline{Data}$ Polling) is equivalent to the data written to this bit at which time the device returns to the read mode and addresses are no longer latched (see Table 5, Write Operation Status). Therefore, the device requires that a valid address to the device be supplied by the system at this particular instance of time for $\overline{Data}$ Polling operations. $\overline{Data}$ Polling must be performed at the memory location which is being programmed.

Any commands written to the chip during the Embedded Program Algorithm will be ignored. If a hardware reset occurs during the programming operation, the data at that particular location will be corrupted.

Programming is allowed in any sequence and across sector boundaries. Beware that a data "0" cannot be programmed back to a "1". Attempting to do so may cause the device to exceed programming time limits (DQ5 = 1) or result in an apparent success, according to the data polling algorithm, but a read from reset/read mode will show that the data is still "0". Only erase operations can convert "0"s to "1"s.

Figure 1 illustrates the Embedded Programming Algorithm using typical command strings and bus operations.

Chip Erase

Chip erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the chip erase command.

Chip erase does *not* require the user to program the device prior to erase. Upon executing the Embedded Erase Algorithm command sequence the device will automatically program and verify the entire memory for an all zero data pattern prior to electrical erase. The erase is performed sequentially on all sectors at the same time (see Table "Erase and Programming Performance"). The system is not required to provide any controls or timings during these operations.

The automatic erase begins on the rising edge of the last $\overline{WE}$ pulse in the command sequence and terminates when the data on DQ7 is "1" (see Write Operation Status section) at which time the device returns to read the mode.

Figure 2 illustrates the Embedded Erase Algorithm using typical command strings and bus operations.

Sector Erase

Sector erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the sector erase command. The sector address (any address location within the desired sector) is latched on the falling edge of $\overline{WE}$, while the command (30H) is latched on the rising edge of $\overline{WE}$. After a time-out of 80 µs from the rising edge of the last sector erase command, the sector erase operation will begin.

Multiple sectors may be erased sequentially by writing the six bus cycle operations as described above. This sequence is followed with writes of the Sector Erase command to addresses in other sectors desired to be sequentially erased. The time between writes must be less than 80 µs otherwise that command will not be accepted and erasure will start. It is recommended that processor interrupts be disabled during this time to guarantee this condition. The interrupts can be re-enabled after the last Sector Erase command is written. A time-out of 80 µs from the rising edge of the last $\overline{WE}$ will initiate the execution of the Sector Erase command(s). If another falling edge of the $\overline{WE}$ occurs within the 80 µs time-out window the timer is reset. (Monitor DQ3 to determine if the sector erase timer window is still open, see section DQ3, Sector Erase Timer.) Any command other than Sector Erase or Erase Suspend during this period will reset the device to the read mode, ignoring the previous command string. In that case, restart the erase on those sectors and allow them to complete.

(Refer to the Write Operation Status section for DQ3, Sector Erase Timer operation.) Loading the sector erase buffer may be done in any sequence and with any number of sectors (0 to 6).

erase buffer may be done in any sequence and with any number of sectors (0 to 6).

Sector erase does *not* require the user to program the device prior to erase. The device automatically programs all memory locations in the sector(s) to be erased prior to electrical erase. When erasing a sector or sectors the remaining unselected sectors are not affected. The system is *not* required to provide any controls or timings during these operations.

The automatic sector erase begins after the 80 µs time out from the rising edge of the $\overline{WE}$ pulse for the last sector erase command pulse and terminates when the data on DQ7, $\overline{Data}$ Polling, is "1" (see Write Operation Status section) at which time the device returns to the read mode. $\overline{Data}$ Polling must be performed at an address within any of the sectors being erased.

Figure 2 illustrates the Embedded Erase Algorithm using typical command strings and bus operations.

Erase Suspend

The Erase Suspend command allows the user to interrupt a Sector Erase operation and then perform data reads from a sector not being erased. This command is applicable ONLY during the Sector Erase operation which includes the time-out period for sector erase. The Erase Suspend command will be ignored if written during the Chip Erase operation or Embedded Program Algorithm. Writing the Erase Suspend command during the Sector Erase time-out results in immediate termination of the time-out period and suspension of the erase operation.

Any other command written during the Erase Suspend mode will be ignored except the Erase Resume command. Writing the Erase Resume command resumes the erase operation. The addresses are "don't-cares" when writing the Erase Suspend or Erase Resume command.

When the Erase Suspend command is written during the Sector Erase operation, the device will take a maximum of 15 µs to suspend the erase operation. When the device has entered the erase-suspended mode, DQ6 will stop toggling. The user must use the address of a sector NOT being erased for reading DQ6 to determine if the erase operation has been suspended. Further writes of the Erase Suspend command are ignored.

When the erase operation has been suspended, the device defaults to the erase-suspend-read mode. Reading data in this mode is the same as reading from the standard read mode except that the data must be read from sectors that have not been erase-suspended.

To resume the operation of Sector Erase, the Resume command (30H) should be written. Any further writes of the Resume command at this point will be ignored. Another Erase Suspend command can be written after the chip has resumed erasing.

Write Operation Status

Table 5. Write Operation Status

	Status	DQ7	DQ6	DQ5	DQ3	
In Progress	Auto-Programming	$\overline{DQ7}$	Toggle	0	0	($\overline{D}$) (Note 1)
	Program/Erase in Auto Erase	0	Toggle	0	1	
Exceeded Time Limits	Auto-Programming	$\overline{DQ7}$	Toggle	1	1	($\overline{D}$) (Note 1)
	Program/Erase in Auto-Erase	0	Toggle	1	1	

Notes:

1. *DQ0, DQ1, DQ2 are reserve pins for future use.*
2. *DQ8 – DQ15 = Don't Care for x16 mode.*
3. *DQ4 for AMD internal use only.*

DQ7
Data Polling

The Am29F200 device features Data Polling as a method to indicate to the host that the embedded algorithms are in progress or completed. During the Embedded Program Algorithm an attempt to read the device will produce the complement of the data last written to DQ7. Upon completion of the Embedded Program Algorithm, an attempt to read the device will produce the true data last written to DQ7. During the Embedded Erase Algorithm, an attempt to read the device will produce a "0" at the DQ7 output. Upon completion of the Embedded Erase Algorithm an attempt to read the device will produce a "1" at the DQ7 output. The flowchart for Data Polling (DQ7) is shown in Figure 3.

For chip erase, the Data Polling is valid after the rising edge of the sixth WE pulse in the six write pulse sequence. For sector erase, the Data Polling is valid after the last rising edge of the sector erase WE pulse. Data Polling must be performed at sector addresses within any of the sectors being erased and **not** a protected sector. Otherwise, the status may not be valid.

Just prior to the completion of Embedded Algorithm operations DQ7 may change asynchronously while the output enable (OE) is asserted low. This means that the device is driving status information on DQ7 at one instant of time and then that byte's valid data at the next instant of time. Depending on when the system samples the DQ7 output, it may read the status or valid data. Even if the device has completed the Embedded Algorithm operations and DQ7 has a valid data, the data outputs on DQ0–DQ6 may be still invalid. The valid data on DQ0–DQ7 will be read on the successive read attempts.

The Data Polling feature is only active during the Embedded Programming Algorithm, Embedded Erase Algorithm, or sector erase time-out (see Table 7).

See Figure 11 for the Data Polling timing specifications and diagrams.

DQ6
Toggle Bit

The Am29F200 also features the "Toggle Bit" as a method to indicate to the host system that the embedded algorithms are in progress or completed.

During an Embedded Program or Erase Algorithm cycle, successive attempts to read (OE toggling) data from the device at any address will result in DQ6 toggling between one and zero. Once the Embedded Program or Erase Algorithm cycle is completed, DQ6 will stop toggling and valid data will be read on *the next* successive attempt. During programming, the Toggle Bit is valid after the rising edge of the fourth WE pulse in the four write pulse sequence. For chip erase, the Toggle Bit is valid after the rising edge of the sixth WE pulse in the six write pulse sequence. For Sector erase, the Toggle Bit is valid after the last rising edge of the sector erase WE pulse. The Toggle Bit is active during the sector time-out.

Either CE or OE toggling will cause DQ6 to toggle. In addition, an Erase Suspend/Resume command will cause DQ6 to toggle. See Figure 12 for the Toggle Bit timing specifications and diagrams.

DQ5
Exceeded Timing Limits

DQ5 will indicate if the program or erase time has exceeded the specified limits (internal pulse count). Under these conditions DQ5 will produce a "1". This is a failure condition which indicates that the program or erase cycle was not successfully completed. Data Polling is the only operating function of the device under this condition. The CE circuit will partially power down the device under these conditions (to approximately 2 mA). The OE and WE pins will control the output disable functions as described in Table 1.1 and 1.2.

The DQ5 failure condition will also appear if a user tries to program a 1 to a location that is previously programmed to 0. In this case the device locks out and never completes the Embedded Program Algorithm. Hence, the system never reads a valid data on DQ7 bit and DQ6 never stops toggling. Once the device has exceeded timing limits, the DQ5 bit will indicate a "1." Please note that this is not a device failure condition since the device was incorrectly used. If this occurs, reset the device.

DQ3
Sector Erase Timer

After the completion of the initial sector erase command sequence the sector erase time-out will begin. DQ3 will remain low until the time-out is complete. Data Polling and Toggle Bit are valid after the initial sector erase command sequence.

If Data Polling or the Toggle Bit indicates the device has been written with a valid erase command, DQ3 may be used to determine if the sector erase timer window is still open. If DQ3 is high ("1") the internally controlled erase cycle has begun; attempts to write subsequent commands (other than Erase Suspend) to the device will be ignored until the erase operation is completed as indicated by Data Polling or Toggle Bit. If DQ3 is low ("0"), the device will accept additional sector erase commands. To insure the command has been accepted, the system software should check the status of DQ3 prior to and following each subsequent sector erase command. If DQ3 were high on the second status check, the command may not have been accepted.

Refer to Table 5: Write Operation Status.

RY/BY
Ready/Busy

The Am29F200 provides a RY/BY open-drain output pin as a way to indicate to the host system that the Embedded Algorithms are either in progress or have been completed. If the output is low, the device is busy with either a program or erase operation. If the output is high, the

device is ready to accept any read/write or erase operation. When the RY/$\overline{BY}$ pin is low, the device will not accept any additional program or erase commands with the exception of the Erase Suspend command. If the Am29F200 is placed in an Erase Suspend mode, the RY/$\overline{BY}$ output will be high.

During programming, the RY/$\overline{BY}$ pin is driven low after the rising edge of the fourth $\overline{WE}$ pulse. During an erase operation, the RY/$\overline{BY}$ pin is driven low after the rising edge of the sixth $\overline{WE}$ pulse. The RY/$\overline{BY}$ pin should be ignored while RESET is at V_{IL}. Refer to Figure 13 for a detailed timing diagram.

Since this is an open-drain output, several RY/$\overline{BY}$ pins can be tied together in parallel with a pull-up resistor to V_{CC}.

$\overline{RESET}$

Hardware Reset

The Am29F200 device may be reset by driving the $\overline{RESET}$ pin to V_{IL}. The $\overline{RESET}$ pin must be kept low (V_{IL}) for at least 500 ns. Any operation in progress will be terminated and the internal state machine will be reset to the read mode 20 µs after the $\overline{RESET}$ pin is driven low. Furthermore, once the $\overline{RESET}$ pin goes high, the device requires an additional 50 ns before it will allow read access. When the $\overline{RESET}$ pin is low, the device will be in the standby mode for the duration of the pulse and all the data output pins will be tri-stated. If a hardware reset occurs during a program or erase operation, the data at that particular location will be indeterminate.

The $\overline{RESET}$ pin may be tied to the system reset input. Therefore, if a system reset occurs during the Embedded Program or Erase Algorithm, the device will be automatically reset to read mode and this will enable the system's microprocessor to read the boot-up firmware from the Flash memory.

Byte/Word Configuration

The $\overline{BYTE}$ pin selects the byte (8-bit) mode or word (16 bit) mode for the Am29F200 device. When this pin is driven high, the device operates in the word (16 bit) mode. The data is read and programmed at DQ0–DQ15. When this pin is driven low, the device operates in byte (8 bit) mode. Under this mode, the DQ15/A-1 pin becomes the lowest address bit and DQ8–DQ14 bits are tristated. However, the command bus cycle is always an 8-bit operation and hence commands are written at DQ0–DQ7 and the DQ8–DQ15 bits are ignored. Refer to Figures 15 and 16 for the timing diagram.

Data Protection

The Am29F200 is designed to offer protection against accidental erasure or programming caused by spurious system level signals that may exist during power transitions. During power up the device automatically resets the internal state machine in the Read mode. Also, with its control register architecture, alteration of the memory contents only occurs after successful completion of specific multi-bus cycle command sequences.

The device also incorporates several features to prevent inadvertent write cycles resulting from V_{CC} power-up and power-down transitions or system noise.

Low V_{CC} Write Inhibit

To avoid initiation of a write cycle during V_{CC} power-up and power-down, the Am29F200 locks out write cycles for $V_{CC} < V_{LKO}$ (see DC Characteristics section for voltages). When $V_{CC} < V_{LKO}$, the command register is disabled, all internal program/erase circuits are disabled, and the device resets to the read mode. The Am29F200 ignores all writes until $V_{CC} > V_{LKO}$. The user must ensure that the control pins are in the correct logic state when $V_{CC} > V_{LKO}$ to prevent uninitentional writes.

Write Pulse "Glitch" Protection

Noise pulses of less than 5 ns (typical) on $\overline{OE}$, $\overline{CE}$, or $\overline{WE}$ will not initiate a write cycle.

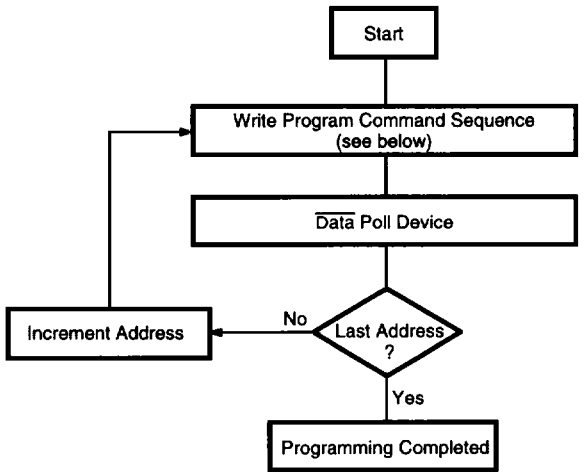
Logical Inhibit

Writing is inhibited by holding any one of $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IH}$, or $\overline{WE} = V_{IH}$. To initiate a write cycle $\overline{CE}$ and $\overline{WE}$ must be a logical zero while $\overline{OE}$ is a logical one.

Power-Up Write Inhibit

Power-up of the device with $\overline{WE} = \overline{CE} = V_{IL}$ and $\overline{OE} = V_{IH}$ will not accept commands on the rising edge of $\overline{WE}$. The internal state machine is automatically reset to the read mode on power-up.

EMBEDDED ALGORITHMS



Program Command Sequence (Address/Command):

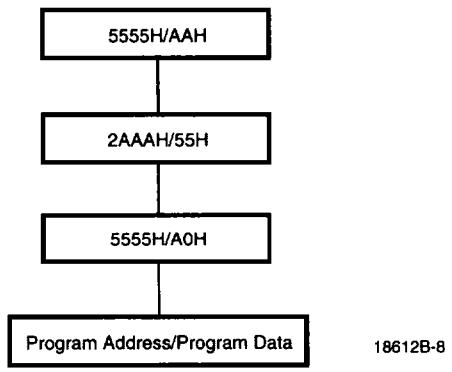
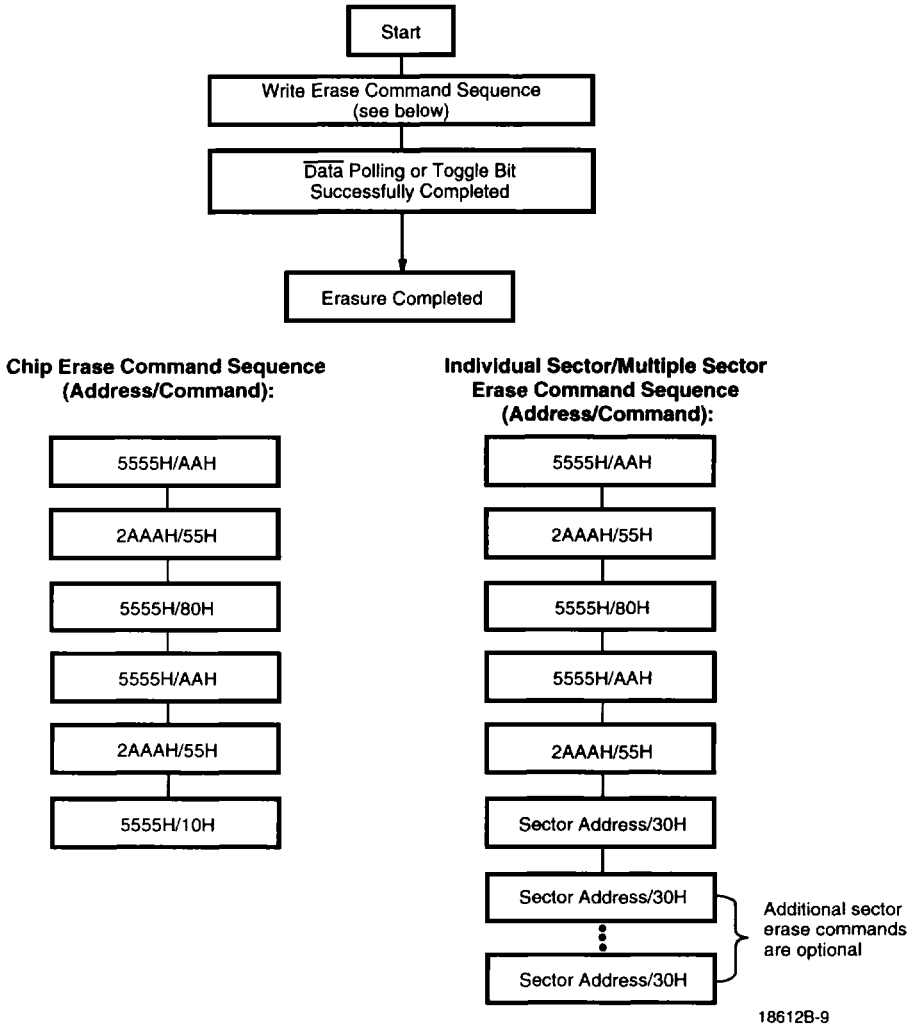


Figure 1. Embedded Programming Algorithm

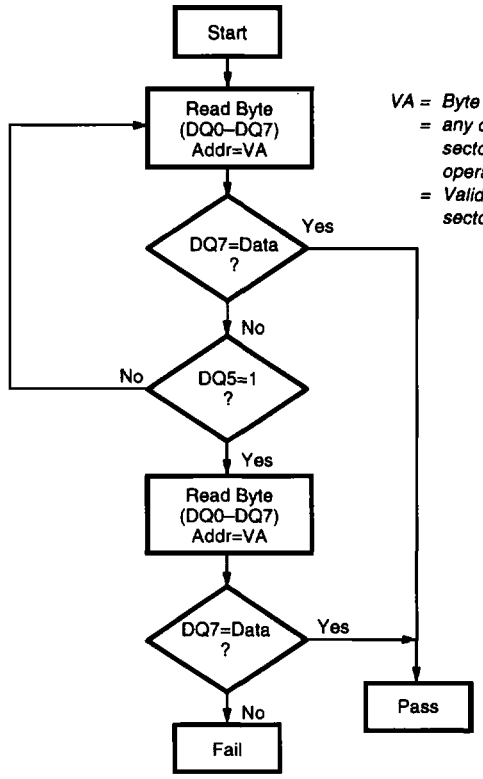
EMBEDDED ALGORITHMS



Note:

1. *To insure the command has been accepted, the system software should check the status of DQ3 prior to and following each subsequent sector erase command. If DQ3 were high on the second status check, the command may not have been accepted.*

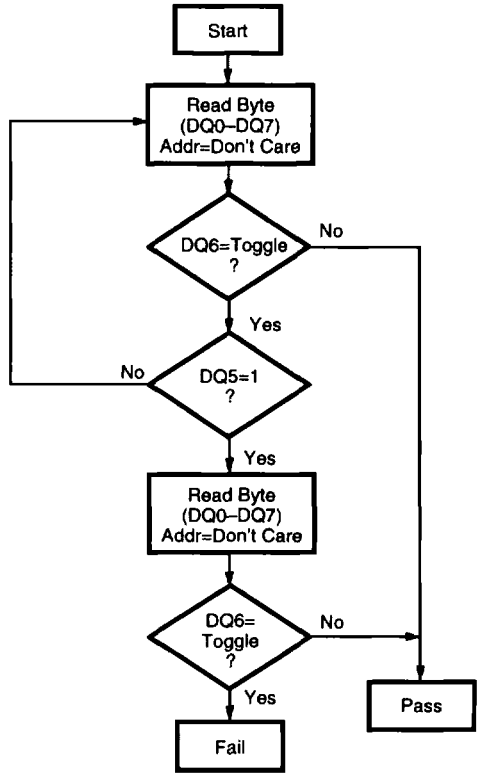
Figure 2. Embedded Erase Algorithm



Note:

1. *DQ7 is rechecked even if DQ5 = "1" because DQ7 may change simultaneously with DQ5.*

Figure 3. $\overline{\text{Data}}$ Polling Algorithm



Note:

1. *DQ6 is rechecked even if DQ5 = "1" because DQ6 may stop toggling at the same time as DQ5 changing to "1".*

Figure 4. Toggle Bit Algorithm

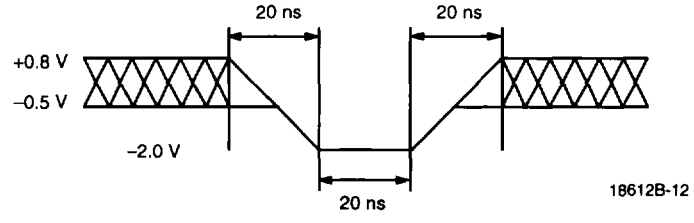


Figure 5. Maximum Negative Overshoot Waveform

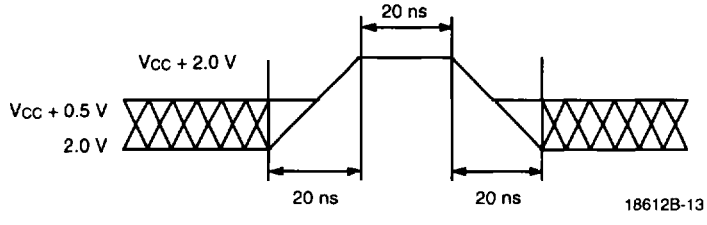


Figure 6. Maximum Positive Overshoot Waveform

ABSOLUTE MAXIMUM RATINGS

Storage Temperature
Plastic Packages ..... –65°C to +125°C

Ambient Temperature
with Power Applied ..... –55°C to +125°C

Voltage with Respect to Ground
All pins except A9 (Note 1) ..... –2.0 V to +7.0 V

V_{CC} (Note 1) ..... –2.0 V to +7.0 V

A9 (Note 2) ..... –2.0 V to +14.0 V

Output Short Circuit Current (Note 3) ..... 200 mA

Notes:

1. *Minimum DC voltage on input or I/O pins is –0.5 V. During voltage transitions, inputs may overshoot V_{SS} to –2.0 V for periods of up to 20 ns. Maximum DC voltage on input and I/O pins is V_{CC} + 0.5 V. During voltage transitions, input and I/O pins may overshoot to V_{CC} + 2.0 V for periods up to 20 ns.*
2. *Minimum DC input voltage on A9 pin is –0.5 V. During voltage transitions, A9 may overshoot V_{SS} to –2.0 V for periods of up to 20 ns. Maximum DC input voltage on A9 is +12.5 V which may overshoot to 14.0 V for periods up to 20 ns.*
3. *No more than one output shorted to ground at a time. Duration of the short circuit should not be greater than one second.*

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices
Ambient Temperature (T_A) ..... 0°C to +70°C

Industrial (I) Devices
Ambient Temperature (T_A) ..... –40°C to +85°C

Extended (E) Devices
Ambient Temperature (T_A) ..... –55°C to +125°C

V_{CC} Supply Voltages
V_{CC} for Am29F200T/B-75 ..... +4.75 V to +5.25 V

V_{CC} for Am29F200T/B-90,
120, 150 ..... +4.50 V to +5.50 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS
TTL/NMOS Compatible

Parameter Symbol	Parameter Description	Test Conditions		Min	Max	Unit
I_{LI}	Input Load Current	V_{IN} = V_{SS} to V_{CC}, V_{CC} = V_{CC} Max			±1.0	µA
I_{LIT}	A9 Input Load Current	V_{CC} = V_{CC} Max, A9 = 12.5 V			50	µA
I_{LO}	Output Leakage Current	V_{OUT} = V_{SS} to V_{CC}, V_{CC} = V_{CC} Max			±1.0	µA
I_{CC1}	V_{CC} Active Current (Note 1)	$\overline{CE}$ = V_{IL}, $\overline{OE}$ = V_{IH}	Byte		40	mA
			Word		50	
I_{CC2}	V_{CC} Active Current (Notes 2, 3)	$\overline{CE}$ = V_{IL}, $\overline{OE}$ = V_{IH}			60	mA
I_{CC3}	V_{CC} Standby Current	V_{CC} = V_{CC} Max, $\overline{CE}$ = V_{IH}, $\overline{OE}$ = V_{IH}			1.0	mA
V_{IL}	Input Low Voltage			–0.5	0.8	V
V_{IH}	Input High Voltage			2.0	V_{CC} + 0.5	V
V_{ID}	Voltage for Autoselect and Temporary Sector Unprotect	V_{CC} = 5.0 Volt		11.5	12.5	V
V_{OL}	Output Low Voltage	I_{OL} = 5.8 mA, V_{CC} = V_{CC} Min			0.45	V
V_{OH}	Output High Voltage	I_{OH} = –2.5 mA, V_{CC} = V_{CC} Min		2.4		V
V_{LKO}	Low V_{CC} Lock-Out Voltage			3.2	4.2	V

Notes:

1. *The I_{CC} current listed includes both the DC operating current and the frequency dependent component (at 6 MHz). The frequency component typically is less than 2 mA/MHz, with $\overline{OE}$ at V_{IH}.*
2. *I_{CC} active while Embedded Program or Erase Algorithm is in progress.*
3. *Not 100% tested.*

DC CHARACTERISTICS (continued)
CMOS Compatible

Parameter Symbol	Parameter Description	Test Conditions		Min	Max	Unit
I_{LI}	Input Load Current	V_{IN} = Vss to Vcc, Vcc = Vcc Max			±1.0	µA
I_{LIT}	A9 Input Load Current	Vcc = Vcc Max, A9 = 12.5 V			50	µA
I_{LO}	Output Leakage Current	V_{OUT} = Vss to Vcc, Vcc = Vcc Max			±1.0	µA
I_{CC1}	Vcc Active Current (Note 1)	$\overline{CE}$ = V_{IL}, $\overline{OE}$ = V_{IH}	Byte		40	mA
			Word		50	
I_{CC2}	Vcc Active Current (Notes 2, 3)	$\overline{CE}$ = V_{IL}, $\overline{OE}$ = V_{IH}			60	mA
I_{CC3}	Vcc Standby Current	Vcc = Vcc Max, $\overline{CE}$ = Vcc ± 0.5 V, $\overline{OE}$ = V_{IH}			100	µA
V_{IL}	Input Low Voltage			–0.5	0.8	V
V_{IH}	Input High Voltage			0.7x Vcc	Vcc +0.3	V
V_{ID}	Voltage for Autoselect and Temporary Sector Unprotect	Vcc = 5.0 V		11.5	12.5	V
V_{OL}	Output Low Voltage	I_{OL} = 5.8 mA, Vcc = Vcc Min			0.45	V
V_{OH1}	Output High Voltage	I_{OH} = –2.5 mA, Vcc = Vcc Min		0.85 Vcc		V
V_{OH2}		I_{OH} = –100 µA, Vcc = Vcc Min		Vcc –0.4		V
V_{LKO}	Low Vcc Lock-out Voltage			3.2	4.2	V

Notes:

1. *The Icc current listed includes both the DC operating current and the frequency dependent component (at 6 MHz). The frequency component typically is less than 2 mA/MHz, with $\overline{OE}$ at V_{IH}.*
2. *Icc active while Embedded Program or Erase Algorithm is in progress.*
3. *Not 100% tested.*

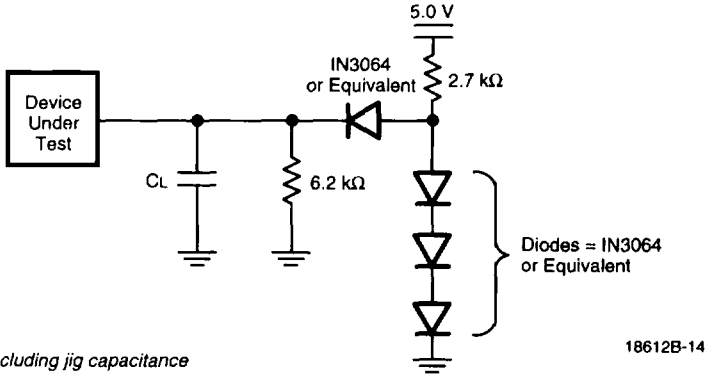
AC CHARACTERISTICS

Read-only Operations Characteristics

Parameter Symbols		Description	Test Setup		-75 (Note 1)	-90 (Note 2)	-120 (Note 2)	-150 (Note 2)	Unit
JEDEC	Standard								
t_{AVAV}	t_{RC}	Read Cycle Time (Note 4)		Min	70	90	120	150	ns
t_{AVQV}	t_{ACC}	Address to Output Delay	$\overline{CE}$ = V_{IL} $\overline{OE}$ = V_{IL}	Max	70	90	120	150	ns
t_{ELQV}	t_{CE}	Chip Enable to Output Delay	$\overline{OE}$ = V_{IL}	Max	70	90	120	150	ns
t_{GLQV}	t_{OE}	Output Enable to Output Delay		Max	30	35	50	55	ns
t_{EHQZ}	t_{DF}	Chip Enable to Output High Z (Notes 3, 4)		Max	20	20	30	35	ns
t_{GHQZ}	t_{DF}	Output Enable to Output High Z (Notes 3, 4)		Max	20	20	30	35	ns
t_{AXQX}	t_{OH}	Output Hold Time From Addresses, $\overline{CE}$ or $\overline{OE}$, Whichever Occurs First		Min	0	0	0	0	ns
	t_{Ready}	$\overline{RESET}$ Pin Low to Read Mode (Note 4)		Max	20	20	20	20	µs
	t_{ELFL} t_{ELFH}	$\overline{CE}$ to $\overline{BYTE}$ Switching Low or High		Max	5	5	5	5	ns

Notes:

1. *Test Conditions:*
   Output Load: 1 TTL gate and 30 pF
   Input rise and fall times: 5 ns
   Input pulse levels: 0.0 V to 3.0 V
   Timing measurement reference level
   Input: 1.5 V
   Output: 1.5 V
2. *Test Conditions:*
   Output Load: 1 TTL gate and 100 pF
   Input rise and fall times: 20 ns
   Input pulse levels: 0.45 V to 2.4 V
   Timing measurement reference level
   Input: 0.8 and 2.0 V
   Output: 0.8 and 2.0 V
3. *Output driver disable time.*
4. *Not 100% tested.*



Notes:

For -75: C_L = 30 pF including jig capacitance

For all others: C_L = 100 pF including jig capacitance

Figure 7. Test Conditions

AC CHARACTERISTICS

Write/Erase/Program Operations

Parameter Symbols								
JEDEC	Standard	Description		-75	-90	-120	-150	Unit
t_{AVAV}	t_{WC}	Write Cycle Time (2)	Min	70	90	120	150	ns
t_{AVWL}	t_{AS}	Address Setup Time	Min	0	0	0	0	ns
t_{WLAX}	t_{AH}	Address Hold Time	Min	45	45	50	50	ns
t_{DVWH}	t_{DS}	Data Setup Time	Min	30	45	50	50	ns
t_{WHDX}	t_{DH}	Data Hold Time	Min	0	0	0	0	ns
	t_{OEH}	Output Enable Hold Time — Read (2)	Min	0	0	0	0	ns
		Output Enable Hold Time — Toggle and $\overline{Data}$ Polling (2)	Min	10	10	10	10	ns
t_{GHWL}	t_{GHWL}	Read Recover Time Before Write ($\overline{OE}$ High to $\overline{WE}$ Low)	Min	0	0	0	0	ns
t_{ELWL}	t_{CS}	$\overline{CE}$ Setup Time	Min	0	0	0	0	ns
t_{WHEH}	t_{CH}	$\overline{CE}$ Hold Time	Min	0	0	0	0	ns
t_{WLWH}	t_{WP}	Write Pulse Width	Min	35	45	50	50	ns
t_{WHWL}	t_{WPH}	Write Pulse Width High	Min	20	20	20	20	ns
t_{WHWH1}	t_{WHWH1}	Byte Programming Operation	Typ	16	16	16	16	µs
t_{WHWH2}	t_{WHWH2}	Sector Erase Operation (1)	Typ	1.5	1.5	1.5	1.5	sec
			Max	30	30	30	30	sec
	t_{VCS}	V_{CC} Set Up Time (2)	Min	50	50	50	50	µs
	t_{VIDR}	Rise Time to V_{ID} (2, 3)	Min	500	500	500	500	ns
	t_{OESP}	$\overline{OE}$ Setup Time to $\overline{WE}$ Active (2, 3)	Min	4	4	4	4	µs
	t_{RP}	$\overline{RESET}$ Pulse Width	Min	500	500	500	500	ns
	t_{FLQZ}	$\overline{BYTE}$ Switching Low to Output High Z (3, 4)	Max	20	30	30	30	ns
	t_{BUSY}	Program/Erase Valid to RY/$\overline{BY}$ Delay (2)	Min	30	35	50	55	ns

Notes:

1. *This does not include the preprogramming time.*
2. *Not 100% tested.*
3. *These timings are for Temporary Sector Unprotect operation.*
4. *Output Driver Disable Time.*

KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS
	Must Be Steady	Will Be Steady
	May Change from H to L	Will Be Changing from H to L
	May Change from L to H	Will Be Changing from L to H
	Don't Care, Any Change Permitted	Changing, State Unknown
	Does Not Apply	Center Line is High-Impedance "Off" State

KS000010

SWITCHING WAVEFORMS

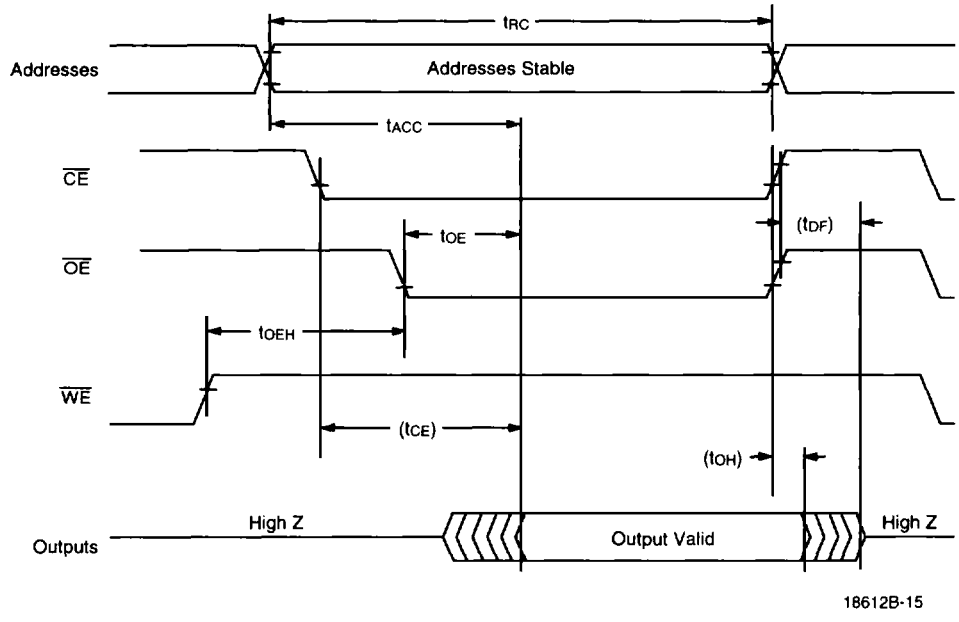
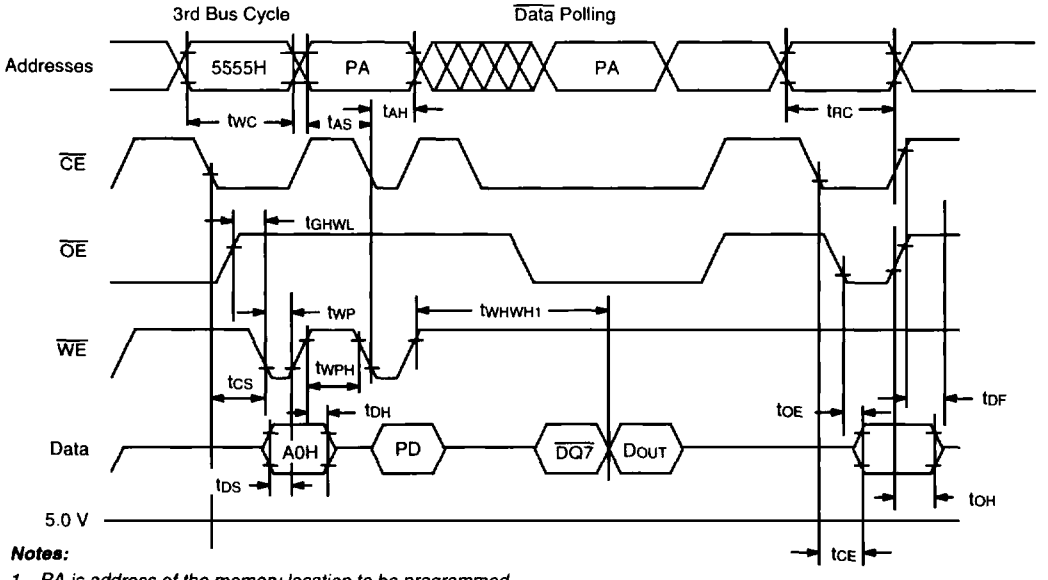


Figure 8. AC Waveforms for Read Operations

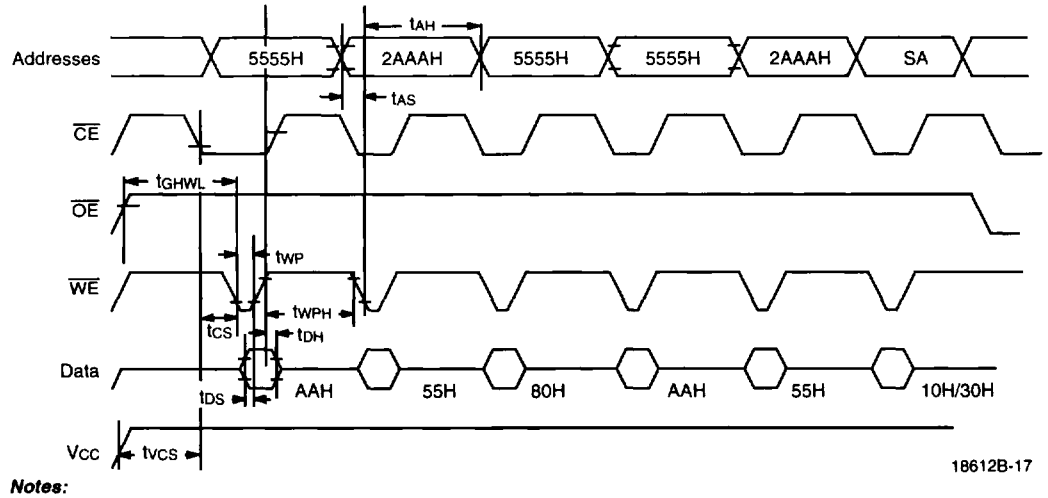
SWITCHING WAVEFORMS



Notes:

1. *PA is address of the memory location to be programmed.*
2. *PD is data to be programmed at byte address.*
3. *$\overline{DQ7}$ is the output of the complement of the data written to the device.*
4. *D_{OUT} is the output of the data written to the device.*
5. *Figure indicates last two bus cycles of four bus cycle sequence.*
6. *These waveforms are for the x16 mode.*

Figure 9. Program Operation Timings

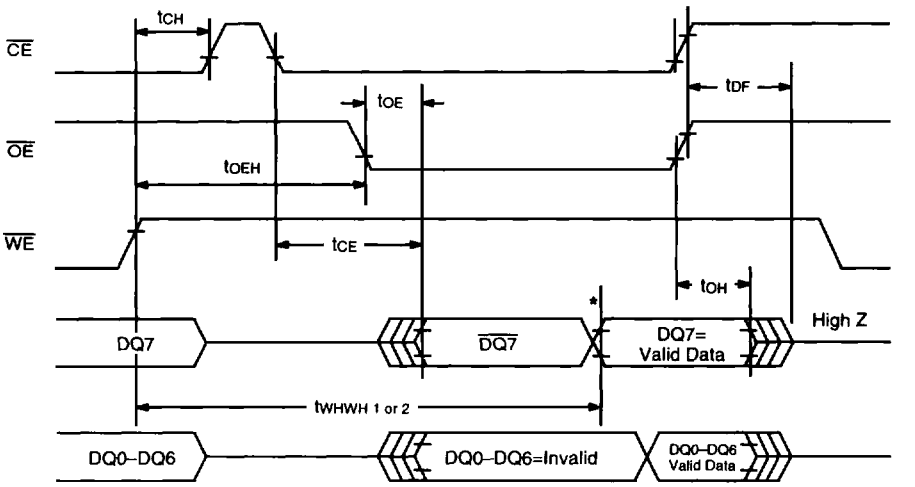


Notes:

1. *SA is the sector address for Sector Erase. Addresses = don't care for Chip Erase.*
2. *These waveforms are for the x16 mode.*

Figure 10. AC Waveforms Chip/Sector Erase Operations

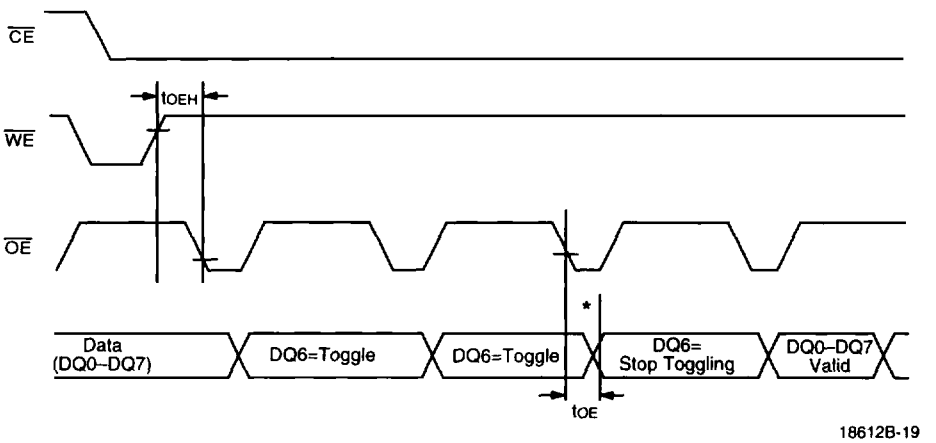
SWITCHING WAVEFORMS



Note:

**DQ7=Valid Data (The device has completed the Embedded operation).*

Figure 11. AC Waveforms for Data Polling During Embedded Algorithm Operations



Note:

**DQ6 stops toggling (The device has completed the Embedded operation).*

Figure 12. AC Waveforms for Toggle Bit During Embedded Algorithm Operations

SWITCHING WAVEFORMS

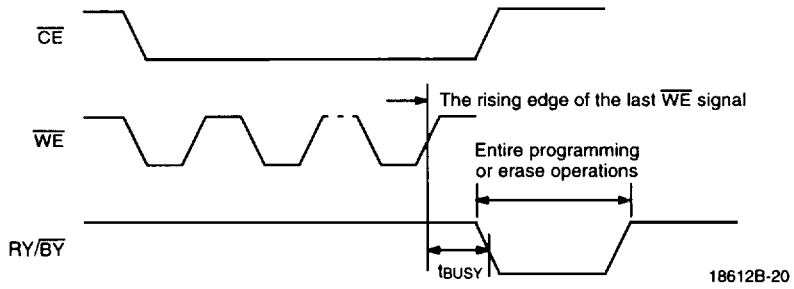


Figure 13. RY/BY Timing Diagram During Program/Erase Operations

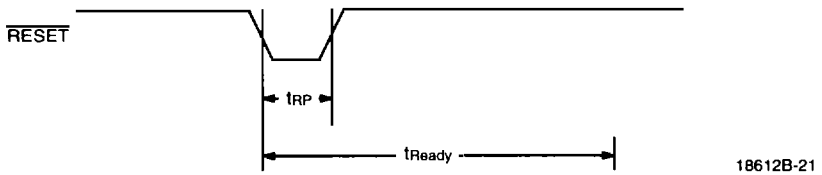


Figure 14. RESET Timing Diagram

SWITCHING WAVEFORMS

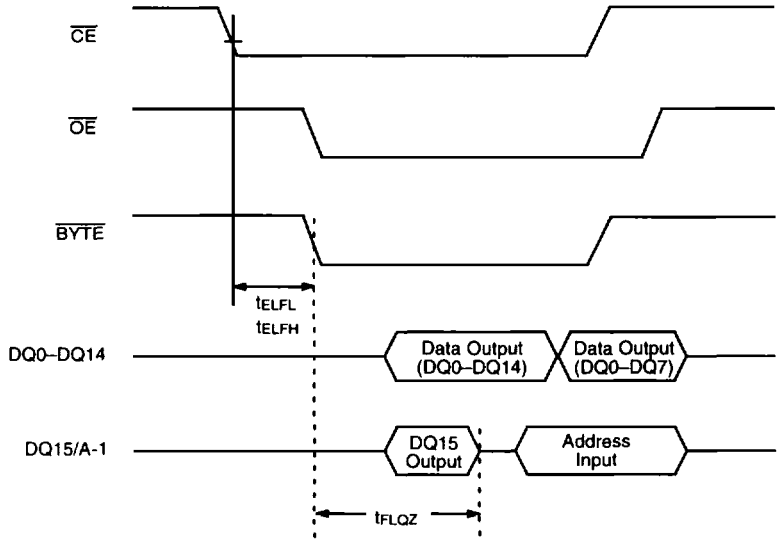


Figure 15. BYTE Timing Diagram for Read Operation

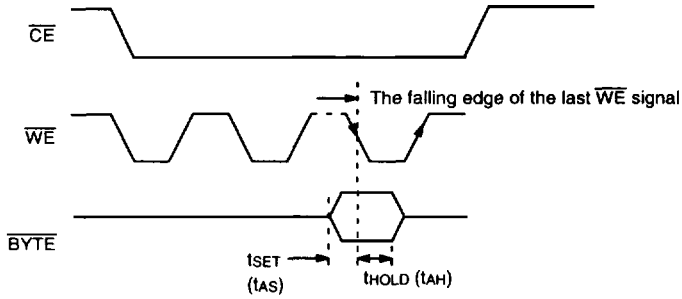
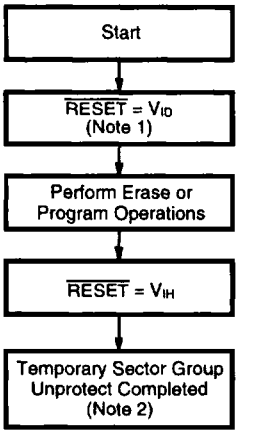


Figure 16. BYTE Timing Diagram for Write Operations



Notes:

1. *All protected sectors unprotected.*
2. *All previously protected sectors are protected once again.*

Figure 17. Temporary Sector Unprotect Algorithm

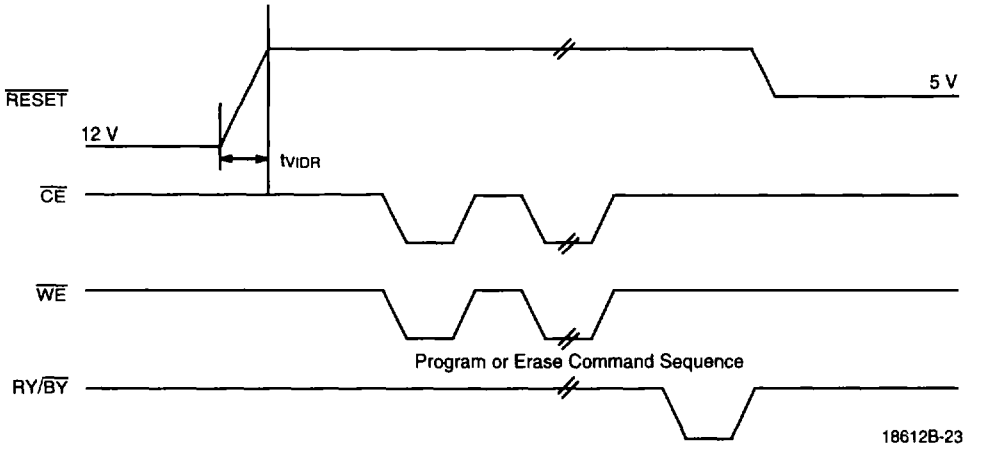


Figure 18. Temporary Sector Unprotect Timing Diagram

AC CHARACTERISTICS

Write/Erase/Program Operations

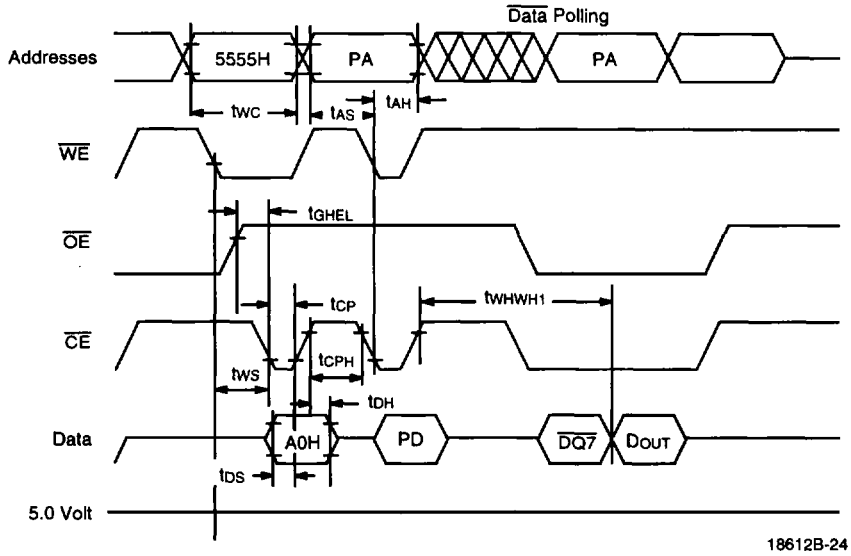
Alternate $\overline{CE}$ Controlled Writes

Parameter Symbols									
JEDEC	Standard	Description			-75	-90	-120	-150	Unit
tAVAV	tWC	Write Cycle Time (Note 2)		Min	70	90	120	150	ns
tAVEL	tAS	Address Setup Time		Min	0	0	0	0	ns
tELAX	tAH	Address Hold Time		Min	45	45	50	50	ns
tDVEH	tDS	Data Setup Time		Min	30	45	50	50	ns
tEHDX	tDH	Data Hold Time		Min	0	0	0	0	ns
	tOES	Output Enable Setup Time		Min	0	0	0	0	ns
	tOEH	Output Enable Hold Time	Read (Note 2)	Min	0	0	0	0	ns
			Toggle and $\overline{Data}$ Polling (2)	Min	10	10	10	10	ns
tGHEL	tGHEL	Read Recover Time Before Write		Min	0	0	0	0	ns
tWLEL	tWS	$\overline{WE}$ Setup Time		Min	0	0	0	0	ns
tEHWH	tWH	$\overline{WE}$ Hold Time		Min	0	0	0	0	ns
tELEH	tCP	$\overline{CE}$ Pulse Width		Min	35	45	50	50	ns
tEHEL	tCPH	$\overline{CE}$ Pulse Width High		Min	20	20	20	20	ns
tWHWH1	tWHWH1	Byte Programming Operation		Typ	16	16	16	16	µs
tWHWH2	tWHWH2	Sector Erase Operation (Note 1)		Typ	1.5	1.5	1.5	1.5	sec
				Max	30	30	30	30	sec
	tFLQZ	$\overline{BYTE}$ Switching Low to Output High Z (2)		Max	20	30	30	30	ns

Notes:

1. *This does not include the preprogramming time.*
2. *Not 100% tested.*

SWITCHING WAVEFORMS



Notes:

1. *PA is address of the memory location to be programmed.*
2. *PD is data to be programmed at byte address.*
3. *$\overline{DQ7}$ is the output of the complement of the data written to the device.*
4. *DOUT is the output of the data written to the device.*
5. *Figure indicates last two bus cycles of four bus cycle sequence.*
6. *These waveforms are for the x16 mode.*

Figure 19. Alternate $\overline{CE}$ Controlled Program Operation Timings

ERASE AND PROGRAMMING PERFORMANCE

Parameter	Limits			Comments
	Typ	Max	Unit	
Sector Erase Time	1.0 (Note 1)	30	sec	Excludes 00H programming prior to erasure
Chip Erase Time	7 (Note 1)	105	sec	Excludes 00H programming prior to erasure
Byte Programming Time	14 (Note 1)	1000 (Note 3)	µs	Excludes system-level overhead (Note 4)
Chip Programming Time	3.6 (Note 1)	25 (Notes 3,5)	sec	Excludes system-level overhead (Note 4)

Notes:

1. *25°C, 5 V V_{CC}, 100,000 cycles.*
2. *Although Embedded Algorithms allow for a longer chip program and erase time, the actual time will be considerably less since bytes program or erase significantly faster than the worst case byte.*
3. *Under worst case condition of 90°C, 4.5 V V_{CC}, 100,000 cycles.*
4. *System-level overhead is defined as the time required to execute the four bus cycle command necessary to program each byte. In the pre-programming step of the Embedded Erase algorithm, all bytes are programmed to 00H before erasure.*
5. *The Embedded Algorithms allow for 48 ms byte program time. DQ5 = "1" only after a byte takes the theoretical maximum time to program. A minimal number of bytes may require significantly more programming pulses than the typical byte. The majority of the bytes will program within one or two pulses. This is demonstrated by the Typical and Maximum Programming Times listed above.*

LATCHUP CHARACTERISTICS

	Min	Max
Input Voltage with respect to V_{SS} on all I/O pins	−1.0 V	V_{CC} + 1.0 V
V_{CC} Current	−100 mA	+100 mA

Includes all pins except V_{CC}. Test conditions: V_{CC} = 5.0 V, one pin at a time.

TSOP PIN CAPACITANCE

Parameter Symbol	Parameter Description	Test Setup	Typ	Max	Unit
C_{IN}	Input Capacitance	V_{IN} = 0	6	7.5	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0	8.5	12	pF
C_{IN2}	Control Pin Capacitance	V_{IN} = 0	8	10	pF

Notes:

1. *Sampled, not 100% tested.*
2. *Test conditions T_A = 25°C, f = 1.0 MHz.*

SO PIN CAPACITANCE

Parameter Symbol	Parameter Description	Test Setup	Typ	Max	Unit
C_{IN}	Input Capacitance	V_{IN} = 0	6	7.5	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0	8.5	12	pF
C_{IN2}	Control Pin Capacitance	V_{PP} = 0	8	10	pF

Notes:

1. *Sampled, not 100% tested.*
2. *Test conditions T_A = 25°C, f = 1.0 MHz.*

DATA RETENTION

Parameter	Test Conditions	Min	Unit
Minimum Pattern Data Retention Time	150°C	10	Years
	125°C	20	Years

DATA SHEET REVISION SUMMARY FOR AM29F200T/AM29F200B

Title

Changed from "Preliminary" to "Final".

Distinctive Characteristics

Added entries for power management, hardware reset, and sector protection.

General Description – Flexible Sector Erase Architecture

Added addresses for x16 configuration to figures.

Tables 3.1 and 3.2 – Sector Address Tables

Added x16 address range.

Sector Protect, Sector Unprotect

Moved information on how to implement Sector Protect and Sector Unprotect, and moved Figures 17 through 20, to the *Am29F200 Data Sheet Supplement for PROM Programmer Manufacturers.*

Table 7 – Command Definitions

Added fourth bus cycle and word/byte information to the Autoselect section.

Table 9 – Embedded Programming Algorithm

Deleted.

Table 10 – Embedded Erase Algorithm

Deleted.

Absolute Maximum Ratings

Changed to reflect currently available packages; corrected errors in the notes.

Figure 14 – $\overline{\text{RESET}}$ Timing Diagram

Removed $\overline{CE}$ and RY/$\overline{BY}$ waveforms.

Figure 17 – Temporary Unprotect Algorithm

Added figure.

Figure 18 – Temporary Sector Unprotect Timing Diagram

Added figure.

Erase and Programming Performance

Added notes 3, 4, and 5.